

CHIP NUMBER

230



.099"
(2.52mm)

.095"
(2.41mm)

PNP EPITAXIAL PLANAR POWER DARLINGTON (FORMERLY 30)**

CONTACT METALLIZATION

Base and emitter: > 30,000 Å Aluminum

Collector: Gold

(Polished silicon or "Chrome Nickel Silver" also available)

Also available on:

MOLY PEDESTAL

Size: .140 Diameter (3.56mm)

Thickness: .010" (0.25mm)

BeO PEDESTAL

Size: .142" x .178" (3.61mm x 4.52mm)

Thickness: .028" (0.71mm)

ASSEMBLY RECOMMENDATIONS

It is advisable that:

a) the chip be eutectically mounted with gold silicon preform 98/2%.

b) 8 mil (0.203mm) aluminum wire be ultrasonically attached to the base and emitter contacts.

Output Base: .022" x .024" (0.56mm x 0.61mm)

Input Base: .015" x .025" (0.38mm x 0.64mm)

Output Emitter: .008" x .033" (0.23mm x 0.84mm)

TYPICAL ELECTRICAL CHARACTERISTICS AT 25°C

The following typical electrical characteristics apply for a completely finished component employing the chip number 230 in a TO-3 or equivalent case:

V _{CEO}	V _{CE(s)} @	I _C	I _B	h _{FE} @	I _C	V _{CE}
> 60V	<2.2V	5A	50mA	>1000	5A	5V
> 80V	<2.2V	5A	50mA	>1000	5A	5V
* > 100V	<2.2V	5A	50mA	>1000	5A	5V
* > 120V	<2.2V	5A	50mA	> 500	5A	5V

V _{CEO}	V _{CEX}	V _{EBO}	f _T	COBO	θ _{JC}
> 60V	70V	>10V	35MHz	<60pF	<2.0°C/W
> 80V	90V	>10V	35MHz	<60pF	<2.0°C/W
> 100V	110V	>10V	35MHz	<60pF	<2.0°C/W
> 120V	130V	>10V	35MHz	<60pF	<2.0°C/W

TYPICAL DEVICE TYPES: SDM3400 - SDM3405, SDM3200 - SDM3205

*h_{FE} available at I_C = 1A, V_{CE} = 5.0V, >1000

**The respective NPN complement is chip number 103.